

Ramesh Raju

List of Publications by Year in descending order

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Version: 2024-02-01

25
papers

253
citations

840119

11
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940134

16
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all docs

25
docs citations

25
times ranked

366
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth, structural, spectral, mechanical and optical properties of pure and metal ions doped sulphamic acid single crystals. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , 2010, 76, 470-475.	2.0	40
2	Structural and optical characterization of AlGaIn/GaN layers. <i>Journal of Crystal Growth</i> , 2014, 401, 527-531.	0.7	23
3	Fabrication of gallium nitride and nitrogen doped single layer graphene hybrid heterostructures for high performance photodetectors. <i>Scientific Reports</i> , 2020, 10, 14507.	1.6	22
4	Effects of indium flow rate on the structural, morphological, optical and electrical properties of InGaIn layers grown by metal organic chemical vapour deposition. <i>Journal of Alloys and Compounds</i> , 2019, 811, 151803.	2.8	19
5	Influence of initial growth stages on AlN epilayers grown by metal organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2015, 414, 69-75.	0.7	18
6	Single-step chemical vapour deposition of anti-pyramid MoS ₂ /WS ₂ vertical heterostructures. <i>Nanoscale</i> , 2021, 13, 4537-4542.	2.8	17
7	Correlation between indium content in monolithic InGaIn/GaN multi quantum well structures on photoelectrochemical activity for water splitting. <i>Journal of Alloys and Compounds</i> , 2017, 706, 629-636.	2.8	16
8	Studies on dislocation and surface morphology of Al _{0.1} Ga _{0.9} In/GaN heterostructures grown by MOCVD. <i>Journal of Alloys and Compounds</i> , 2014, 616, 363-371.	2.8	15
9	Structural, morphological, optical and electrical characterization of InGaIn/GaN MQW structures for optoelectronic applications. <i>Applied Surface Science</i> , 2019, 476, 993-999.	3.1	15
10	Controlled growth of gallium nitride nanowires on silicon and their utility in high performance Ultraviolet-A photodetectors. <i>Sensors and Actuators A: Physical</i> , 2021, 332, 113189.	2.0	13
11	Enhancement of visible light photodetector performance for ultrafast switching using flower shaped gallium nitride nanostructures. <i>Scripta Materialia</i> , 2021, 194, 113711.	2.6	12
12	Controlled nucleation and growth of nanostructures by employing surface modified GaN based layers/heterostructures as bottom layer. <i>RSC Advances</i> , 2014, 4, 7112.	1.7	9
13	Electronic excitation induced structural and optical modifications in InGaIn/GaN quantum well structures grown by MOCVD. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017, 394, 81-88.	0.6	9
14	The effect of growth temperature on structural quality of AlInGaIn/AlN/GaN heterostructures grown by MOCVD. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 5373-5380.	1.1	7
15	MOVPE growth of GaN on patterned 6-inch Si wafer. <i>Journal of Physics Communications</i> , 2020, 4, 045010.	0.5	6
16	Structural, surface potential and optical studies of AlGaIn based double heterostructures irradiated by 120 MeV Si ⁹⁺ swift heavy ions. <i>Journal of Alloys and Compounds</i> , 2016, 679, 94-103.	2.8	3
17	Effect of spiral-like islands on structural quality, optical and electrical performance of InGaIn/GaN heterostructures grown by metal organic chemical vapour deposition. <i>Materials Science in Semiconductor Processing</i> , 2022, 142, 106479.	1.9	3
18	Influence of InGaIn interlayer thickness on GaN layers grown by metal organic chemical vapour deposition. <i>Applied Physics A: Materials Science and Processing</i> , 2019, 125, 1.	1.1	2

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19	Influence of AlN interlayer on AlGa _N /Ga _N heterostructures grown by metal organic chemical vapour deposition. Materials Chemistry and Physics, 2021, 259, 124003.	2.0	2
20	Investigation on structural, optical and electrical properties of Cp2Mg flow varied p-GaN grown by MOCVD. AIP Conference Proceedings, 2016, , .	0.3	1
21	Blue-Green-Red Emission From the InGa _N /Ga _N Heterostructures Grown By Metal Organic Chemical Vapour Deposition. Materials Today: Proceedings, 2017, 4, 12577-12581.	0.9	1
22	Effect of Al-mole fraction in Al _x Ga _{1-x} N grown by MOCVD. , 2014, , .		0
23	Oxygen ion irradiation on AlGa _N /Ga _N heterostructure grown on silicon substrate by MOCVD method. AIP Conference Proceedings, 2015, , .	0.3	0
24	Growth of AlN nanostructure on GaN using MOCVD. AIP Conference Proceedings, 2015, , .	0.3	0
25	Growth and characterization of In _x Ga _{1-x} N/GaN single quantum well prepared by MOCVD. AIP Conference Proceedings, 2015, , .	0.3	0